

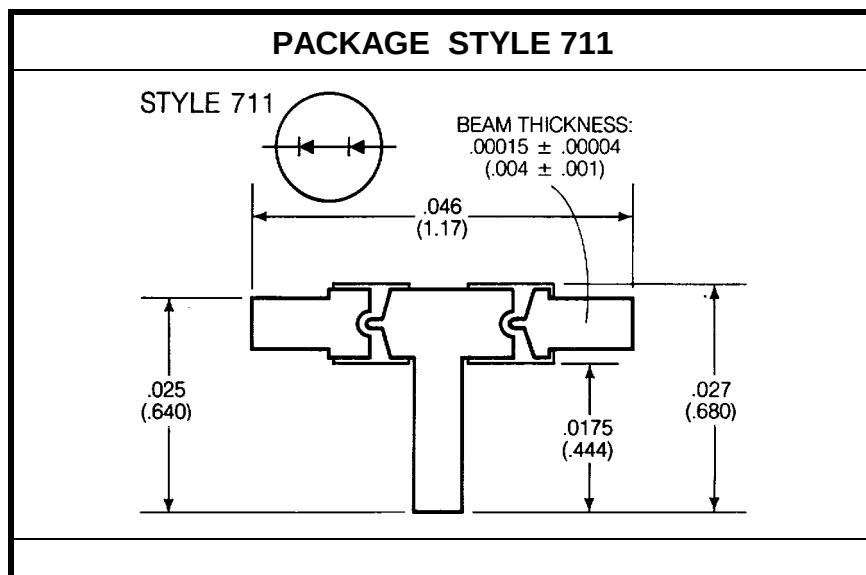
BEAM LEAD SCHOTTKY DIODE

DESCRIPTION:

The **ASI HSCH5531** is a Low Barrier Beam Lead Schottky Diode Designed for K-Band Mixer Applications.

MAXIMUM RATINGS

I_F	25 mA
V_R	4.0 V
P_{DISS}	150 mW @ $T_A = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +175 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10\text{ }\mu\text{A}$		4.0			V
V_F	$I_F = 1.0\text{ mA}$				375	mV
ΔV_F	$I_F = 1.0\text{ mA}$				10	mV
I_R	$V_R = 1.0\text{ V}$				100	nA
R_D	$I_F = 5.0\text{ mA}$				20	Ω
ΔR_D	$I_F = 5.0\text{ mA}$				3.0	Ω
C_T	$V_R = 0\text{ V}$	$f = 1.0\text{ MHz}$			0.10	pF
ΔC_T	$V_R = 0\text{ V}$	$f = 1.0\text{ MHz}$			0.02	pF
TSS	Zero Bias, Zero Bias,			-46		dBm
γ	$P_{IN} = -30\text{ dBm}$			17		mV/μW
R_v	Video Bandwidth = 2.0 MHz			1.4		MΩ